

SN74LV6T17 ヘキサ・シュミット・トリガ・バッファ、統合変換機能付き

1 特長

- 幅広い動作範囲：1.8V~5.5V
- 単一電源電圧トランスレータ（「LVxT 拡張入力電圧」を参照）：
 - 昇圧変換：
 - 1.2V から 1.8V
 - 1.5V から 2.5V
 - 1.8V から 3.3V
 - 3.3V から 5.0V
 - 降圧変換：
 - 5.0V、3.3V、2.5V から 1.8V
 - 5.0V、3.3V から 2.5V
 - 5.0V から 3.3V
- 5.5V 許容入力ピン
- 標準ピン配置をサポート
- 5V または 3.3V の V_{CC} で最大 150Mbps
- JESD 17 準拠で 250mA 超のラッチアップ性能

2 アプリケーション

- デジタル信号のイネーブルまたはディスエーブル
- インジケータ LED の制御
- 通信モジュールとシステム・コントローラ間の変換

3 概要

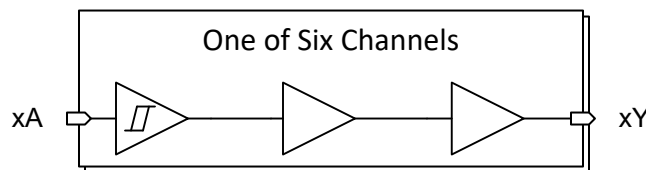
SN74LV6T17 デバイスは、シュミット・トリガ入力の 6 つの独立したインバータを内蔵しています。各ゲートはブール関数 $Y = A$ を正論理で実行します。出力レベルは電源電圧 (V_{CC}) を基準としており、1.8V、2.5V、3.3V、5V の CMOS レベルをサポートしています。

入力は低スレッショルド回路を使用して設計され、低電圧 CMOS 入力の昇圧変換（例：1.2V 入力から 1.8V 出力、1.8V 入力から 3.3V 出力）をサポートします。また、5V 許容入力ピンにより、降圧変換（例：3.3V から 2.5V 出力）が可能です。

パッケージ情報

| 部品番号 | パッケージ ⁽¹⁾ | パッケージ・サイズ ⁽²⁾ | 本体サイズ (公称) ⁽³⁾ |
|------------|----------------------|--------------------------|---------------------------|
| SN74LV6T17 | BQA (WQFN, 14) | 3mm × 2.5mm | 3mm × 2.5mm |
| | PW (TSSOP, 14) | 5mm × 6.4mm | 5mm × 4.4mm |

- (1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。
- (2) パッケージ・サイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。
- (3) 本体サイズ (長さ × 幅) は公称値であり、ピンは含まれません。



概略論理図 (正論理)



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4 Revision History

| DATE | REVISION | NOTES |
|-----------|----------|-----------------|
| June 2023 | * | Initial Release |

5 Pin Configuration and Functions

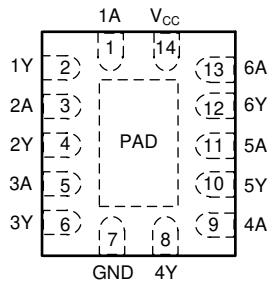


图 5-1. SN74LV6T17 BQA Package, 14-Pin WQFN (Top View)

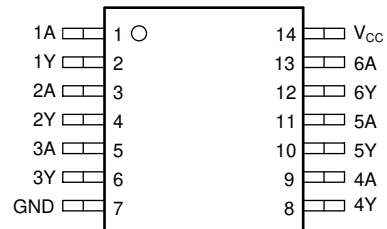


图 5-2. SN74LV6T17 PW Package, 14-Pin TSSOP (Top View)

表 5-1. Pin Functions

| NAME | PIN | | TYPE ⁽¹⁾ | DESCRIPTION |
|----------------------------|-----|----|---------------------|---|
| | BQA | PW | | |
| 1A | | | I | Channel 1, Input A |
| 1Y | | | O | Channel 1, Output Y |
| 2A | | | I | Channel 2, Input A |
| 2Y | | | O | Channel 2, Output Y |
| 3A _{CC} | | | I | Channel 3, Input A |
| 3Y | | | O | Channel 3, Output Y |
| GND | | | G | Ground |
| 4Y | | | O | Channel 4, Output Y |
| 4A | | | I | Channel 4, Input A |
| 5Y | | | O | Channel 5, Output Y |
| 5A | | | I | Channel 5, Input A |
| 6Y | | | O | Channel 6, Output Y |
| 6A | | | I | Channel 6, Input A |
| V _{CC} | | | P | Positive Supply |
| Thermal Pad ⁽²⁾ | | | — | The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply. |

(1) I = input, O = output, I/O = input or output, G = ground, P = power.

(2) BQA package only.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

| | | MIN | MAX | UNIT |
|------------------|---|---|-----------------------|--------|
| V _{CC} | Supply voltage range | -0.5 | 7 | V |
| V _I | Input voltage range ⁽²⁾ | -0.5 | 7 | V |
| V _O | Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾ | -0.5 | 7 | V |
| V _O | Output voltage range ⁽²⁾ | -0.5 | V _{CC} + 0.5 | V |
| I _{IK} | Input clamp current | V _I < -0.5 V | | -20 mA |
| I _{OK} | Output clamp current | V _O < -0.5 V or V _O > V _{CC} + 0.5 V | | ±20 mA |
| I _O | Continuous output current | V _O = 0 to V _{CC} | | ±25 mA |
| | Continuous output current through V _{CC} or GND | | | ±50 mA |
| T _{stg} | Storage temperature | -65 | 150 | °C |

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

6.2 ESD Ratings

| | | VALUE | UNIT |
|--------------------|-------------------------|---|-------|
| V _(ESD) | Electrostatic discharge | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾ | ±2000 |
| | | Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾ | ±1000 |

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

| Spec | Description | Condition | MIN | MAX | UNIT |
|-----------------|------------------------------------|------------------------------------|------|-----------------|------|
| V _{CC} | Supply voltage | | 1.6 | 5.5 | V |
| V _I | Input voltage | | 0 | 5.5 | V |
| V _O | Output voltage | | 0 | V _{CC} | V |
| V _{IH} | High-level input voltage | V _{CC} = 1.65 V to 2 V | 1.1 | | V |
| | | V _{CC} = 2.25 V to 2.75 V | 1.28 | | |
| | | V _{CC} = 3 V to 3.6 V | 1.45 | | |
| | | V _{CC} = 4.5 V to 5.5 V | 2 | | |
| V _{IL} | Low-Level input voltage | V _{CC} = 1.65 V to 2 V | | 0.5 | V |
| | | V _{CC} = 2.25 V to 2.75 V | | 0.65 | |
| | | V _{CC} = 3 V to 3.6 V | | 0.75 | |
| | | V _{CC} = 4.5 V to 5.5 V | | 0.85 | |
| I _O | Output current | V _{CC} = 1.6 V to 2 V | | ±3 | mA |
| | | V _{CC} = 2.25 V to 2.75 V | | ±7 | |
| | | V _{CC} = 3.3 V to 5.0 V | | ±15 | |
| Δt/Δv | Input transition rise or fall rate | V _{CC} = 1.6 V to 5.0 V | | 20 | ns/V |
| T _A | Operating free-air temperature | | -40 | 125 | °C |

6.4 Thermal Information

| THERMAL METRIC ⁽¹⁾ | | SN74LV6T17 | | UNIT |
|-------------------------------|--|------------|------------|------|
| | | BQA (WQFN) | PW (TSSOP) | |
| | | 14 PINS | 14 PINS | |
| R _{θJA} | Junction-to-ambient thermal resistance | 88.3 | 151.0 | °C/W |
| R _{θJC(top)} | Junction-to-case (top) thermal resistance | 90.9 | 80.0 | °C/W |
| R _{θJB} | Junction-to-board thermal resistance | 56.8 | 94.2 | °C/W |
| Ψ _{JT} | Junction-to-top characterization parameter | 9.9 | 28.0 | °C/W |
| Y _{JB} | Junction-to-board characterization parameter | 56.7 | 93.6 | °C/W |
| R _{θJC(bot)} | Junction-to-case (bottom) thermal resistance | 33.4 | N/A | °C/W |

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | V _{CC} | T _A = 25°C | | | -40°C to 125°C | | | UNIT |
|------------------------------------|--|------------------|-----------------------|---------------------|----------------------|----------------|------|-------|------|
| | | | MIN | TYP | MAX | MIN | TYP | MAX | |
| V _{T+} | Positive-going input threshold voltage | 1.65 V to 2 V | 0.6 | | 1.2 | 0.5 | | 1.27 | V |
| | | 2.25 V to 2.75 V | 0.73 | | 1.39 | 0.64 | | 1.44 | |
| | | 3 V to 3.6 V | 0.88 | | 1.59 | 0.80 | | 1.63 | |
| | | 4.5 V to 5.5 V | 1.15 | | 2.03 | 1.1 | | 2.07 | |
| V _{T-} | Negative-going input threshold voltage | 1.65 V to 2 V | 0.225 | | 0.685 | 0.185 | | 0.755 | V |
| | | 2.25 V to 2.75 V | 0.295 | | 0.775 | 0.265 | | 0.805 | |
| | | 3 V to 3.6 V | 0.385 | | 0.875 | 0.345 | | 0.895 | |
| | | 4.5 V to 5.5 V | 0.535 | | 1.075 | 0.495 | | 1.085 | |
| ΔV _T | Hysteresis (V _{T+} - V _{T-}) | 1.65 V to 2 V | 0.35 | | 0.68 | 0.28 | | 0.8 | V |
| | | 2.25 V to 2.75 V | 0.4 | | 0.77 | 0.33 | | 0.87 | |
| | | 3 V to 3.6 V | 0.44 | | 0.88 | 0.38 | | 0.91 | |
| | | 4.5 V to 5.5 V | 0.53 | | 1.2 | 0.51 | | 1.4 | |
| V _{OH} | I _{OH} = -50 uA | 1.65 V to 5.5 V | V _{CC} -0.1 | | V _{CC} -0.1 | | | | V |
| | I _{OH} = -2 mA | 1.65 V to 2 V | 1.28 | 1.7 ⁽¹⁾ | 1.21 | | | | |
| | I _{OH} = -3 mA | 2.25 V to 2.75 V | 2 | 2.4 ⁽¹⁾ | 1.93 | | | | |
| | I _{OH} = -5.5 mA | 3 V to 3.6 V | 2.6 | 3.08 ⁽¹⁾ | 2.49 | | | | |
| | I _{OH} = -8 mA | 4.5 V to 5.5 V | 4.1 | 4.65 ⁽¹⁾ | 3.95 | | | | |
| V _{OL} | I _{OL} = 50 uA | 1.65 V to 5.5 V | | | 0.1 | | 0.1 | V | |
| | I _{OL} = 2 mA | 1.65 V to 2 V | | 0.1 ⁽¹⁾ | 0.2 | | 0.25 | | |
| | I _{OL} = 3 mA | 2.25 V to 2.75 V | | 0.1 ⁽¹⁾ | 0.15 | | 0.2 | | |
| | I _{OL} = 5.5 mA | 3 V to 3.6 V | | 0.2 ⁽¹⁾ | 0.2 | | 0.25 | | |
| | I _{OL} = 8 mA | 4.5 V to 5.5 V | | 0.3 ⁽¹⁾ | 0.3 | | 0.35 | | |
| I _I | V _I = 0 V or V _{CC} | 0 V to 5.5 V | | | ±0.1 | | ±1 | μA | |
| I _{CC} | V _I = 0 V or V _{CC} , I _O = 0; open on loading | 1.65 V to 5.5 V | | | 2 | | 20 | μA | |
| ΔI _{CC} | One input at 0.3 V or 3.4 V, other inputs at 0 or V _{CC} , I _O = 0 | 5.5 V | | | 1.35 | | 1.5 | mA | |
| | One input at 0.3 V or 1.1 V, other inputs at 0 or V _{CC} , I _O = 0 | 1.8 V | | | 10 | | 20 | μA | |
| C _I | V _I = V _{CC} or GND | 5 V | | 4 | 10 | | 10 | pF | |
| C _O | V _O = V _{CC} or GND | 5 V | | 3 | | | | pF | |
| C _{PD} ^{(2) (3)} | No load, F = 1Mhz | 5 V | | 14 | | | | pF | |

(1) Typical value at nearest nominal voltage (1.8 V, 2.5 V, 3.3 V, and 5 V)

(2) C_{PD} is used to determine the dynamic power consumption, per channel.

(3) P_D = V_{CC}² × F_I × (C_{PD} + C_L) where F_I = input frequency, C_L = output load capacitance, V_{CC} = supply voltage.

6.6 Switching Characteristics

over operating free-air temperature range; (unless otherwise noted). See *Parameter Measurement Information*

| PARAMETER | FROM (INPUT) | TO (OUTPUT) | V _{CC} | LOAD CAPACITANCE | T _A = 25°C | | | -40°C to 125°C | | | UNIT |
|-----------------|-----------------------|-------------|-----------------|-----------------------|-----------------------|------|------|----------------|------|------|------|
| | | | | | MIN | TYP | MAX | MIN | TYP | MAX | |
| t _{PD} | A | Y | 1.8 V | C _L = 15pF | 8.85 | 14 | 19.7 | 7.45 | 15.5 | 22.8 | nS |
| | | | | C _L = 50pF | 10.8 | 17.1 | 23.3 | 9.07 | 18.4 | 26.7 | |
| | | | 2.5 V | C _L = 15pF | 6.44 | 8.9 | 11 | 5.42 | 9.6 | 13.4 | |
| | | | | C _L = 50pF | 7.94 | 10.8 | 13.2 | 6.59 | 11.7 | 16 | |
| | | | 3.3 V | C _L = 15pF | 5.24 | 6.9 | 8.4 | 4.42 | 7.5 | 10.2 | |
| | | | | C _L = 50pF | 6.58 | 8.5 | 10.1 | 5.41 | 9.1 | 12.2 | |
| 5 V | C _L = 15pF | 4.09 | 5.1 | 6.2 | 3.29 | 5.5 | 7.7 | | | | |
| | C _L = 50pF | 5.06 | 6.4 | 7.7 | 4.07 | 6.9 | 9.4 | | | | |

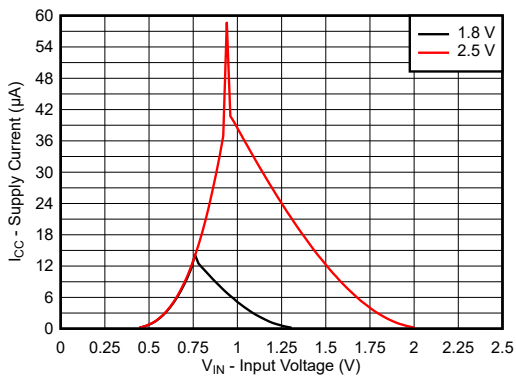
6.7 Noise Characteristics

V_{CC} = 5 V, C_L = 50 pF, T_A = 25°C

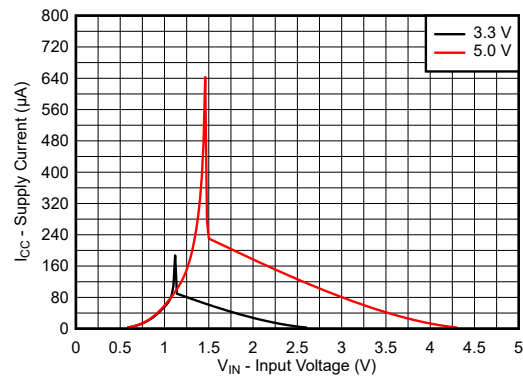
| PARAMETER | DESCRIPTION | MIN | TYP | MAX | UNIT |
|--------------------|---|------|------|-----|------|
| V _{OL(P)} | Quiet output, maximum dynamic V _{OL} | | 0.9 | 0.8 | V |
| V _{OL(V)} | Quiet output, minimum dynamic V _{OL} | -0.8 | -0.3 | | V |
| V _{OH(V)} | Quiet output, minimum dynamic V _{OH} | 4.4 | 5 | | V |
| V _{IH(D)} | High-level dynamic input voltage | 2.1 | | | V |
| V _{IL(D)} | Low-level dynamic input voltage | | | 0.5 | V |

7 Typical Characteristics

T_A = 25°C (unless otherwise noted)



7-1. Supply Current Across Input Voltage 1.8-V and 2.5-V Supply



7-2. Supply Current Across Input Voltage 3.3-V and 5.0-V Supply

7 Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$ (unless otherwise noted)

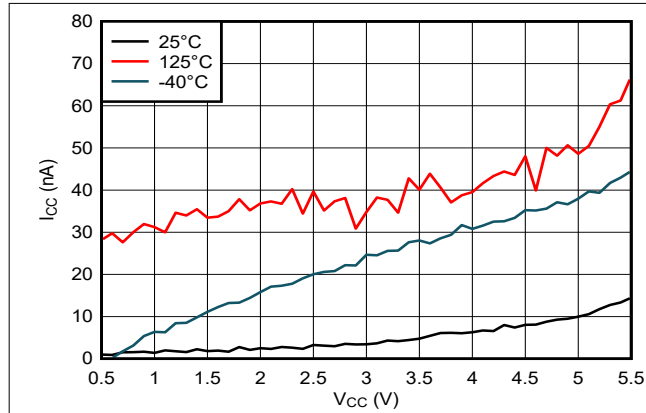


Figure 7-3. Supply Current Across Supply Voltage

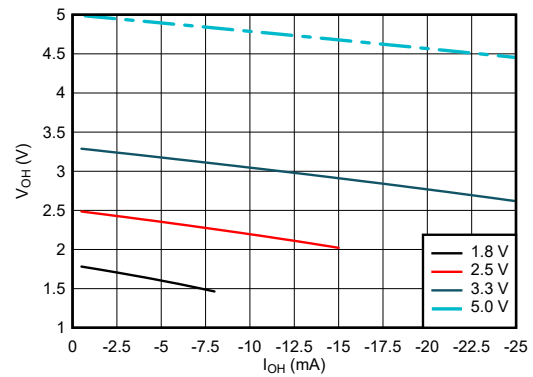


Figure 7-4. Output Voltage vs Current in HIGH State

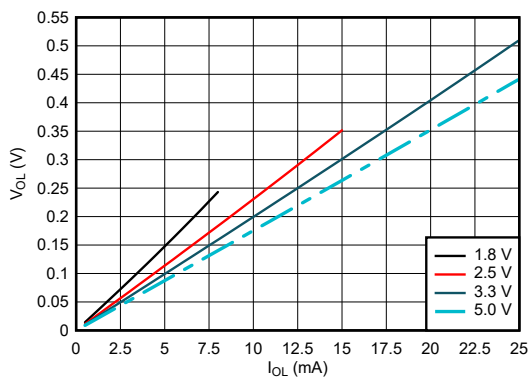


Figure 7-5. Output Voltage vs Current in LOW State

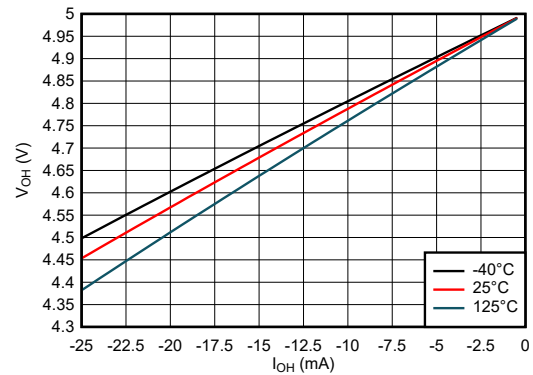


Figure 7-6. Output Voltage vs Current in HIGH State; 5-V Supply

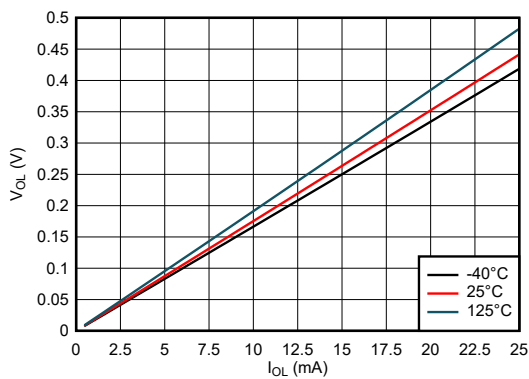


Figure 7-7. Output Voltage vs Current in LOW State; 5-V Supply

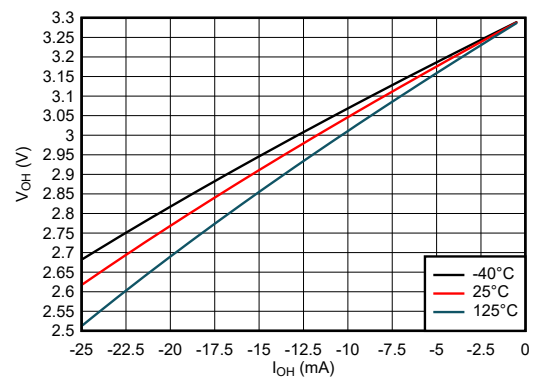


Figure 7-8. Output Voltage vs Current in HIGH State; 3.3-V Supply

7 Typical Characteristics (continued)

$T_A = 25^\circ\text{C}$ (unless otherwise noted)

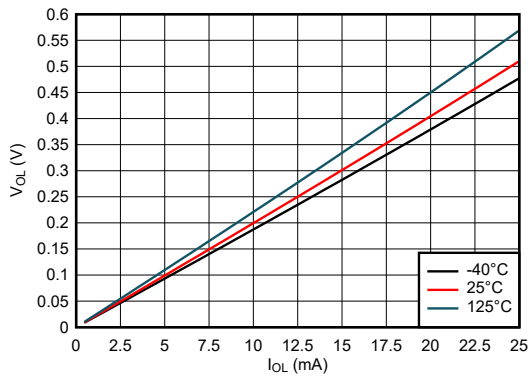


图 7-9. Output Voltage vs Current in LOW State; 3.3-V Supply

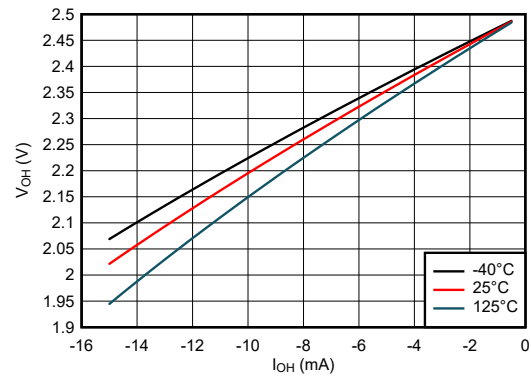


图 7-10. Output Voltage vs Current in HIGH State; 2.5-V Supply

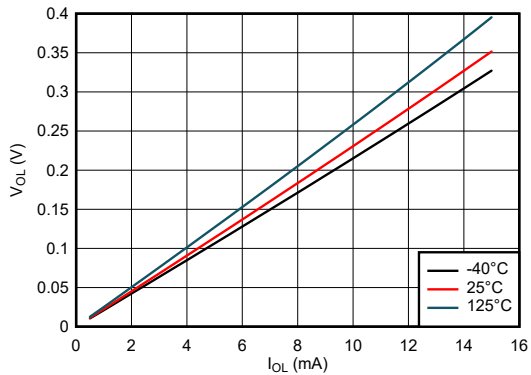


图 7-11. Output Voltage vs Current in LOW State; 2.5-V Supply

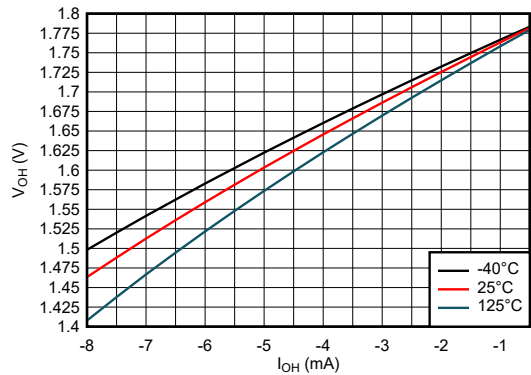


图 7-12. Output Voltage vs Current in HIGH State; 1.8-V Supply

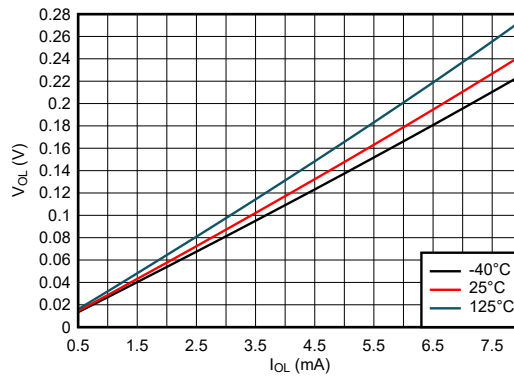


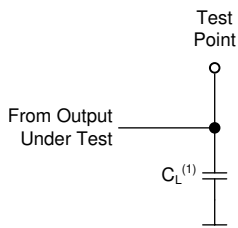
图 7-13. Output Voltage vs Current in LOW State; 1.8-V Supply

8 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1 \text{ MHz}$, $Z_O = 50 \ \Omega$.

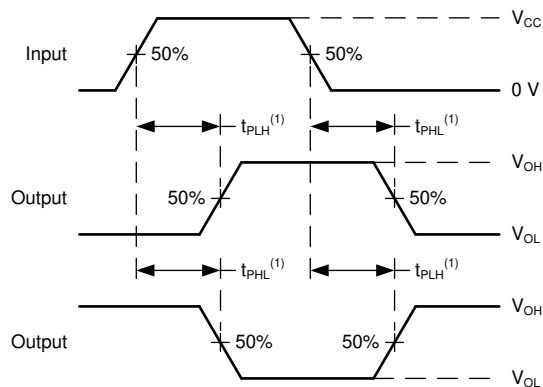
For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



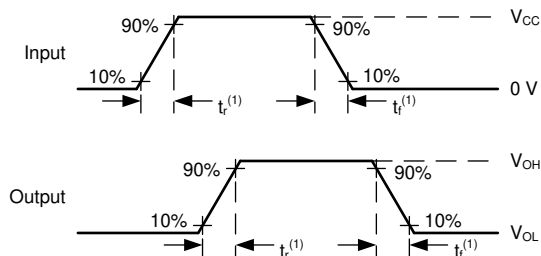
(1) C_L includes probe and test-fixture capacitance.

8-1. Load Circuit for Push-Pull Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd} .

8-2. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t .

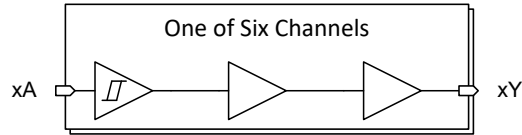
8-3. Voltage Waveforms, Input and Output Transition Times

9 Detailed Description

9.1 Overview

The SN74LV6T17 device contains six independent Buffers with Schmitt-trigger inputs. Each gate performs the Boolean function $Y = A$ in positive logic. The output level is referenced to the supply voltage (V_{CC}) and supports 1.8-V, 2.5-V, 3.3-V, and 5-V CMOS levels.

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 平衡な CMOS プッシュプル出力

このデバイスには、平衡な CMOS プッシュプル出力が内蔵されています。「平衡な」という用語は、デバイスが同様の電流をシンクおよびソースできることを示します。このデバイスは駆動能力を備えており、軽負荷に高速エッジが生成されるため、リングングを防ぐために配線と負荷の条件を考慮する必要があります。さらに、このデバイスの出力は、デバイスを損傷することなく維持できる以上に大きな電流を駆動できます。過電流による損傷を防止するため、デバイスの出力電力を制限することが重要です。「絶対最大定格」で定義されている電気的および熱的制限を常に順守してください。

未使用のプッシュプル CMOS 出力は、未接続のままにする必要があります。

9.3.2 Clamp Diode Structure

The outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only as shown in [図 9-1](#).

注意

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

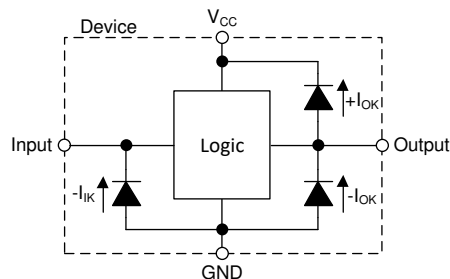


図 9-1. Electrical Placement of Clamping Diodes for Each Input and Output

9.3.3 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the

inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see [Understanding Schmitt Triggers](#).

9.3.4 LVxT Enhanced Input Voltage

The SN74LV6T17 belongs to TI's LVxT family of logic devices with integrated voltage level translation. This family of devices was designed with reduced input voltage thresholds to support up-translation, and inputs tolerant of signals with up to 5.5 V levels to support down-translation. The output voltage will always be referenced to the supply voltage (V_{CC}), as described in the *Electrical Characteristics* table. For proper functionality, input signals must remain at or below the specified $V_{IH(MIN)}$ level for a HIGH input state, and at or below the specified $V_{IL(MAX)}$ for a LOW input state. [Figure 9-2](#) shows the typical V_{IH} and V_{IL} levels for the LVxT family of devices, as well as the voltage levels for standard CMOS devices for comparison.

The inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law ($R = V \div I$).

The inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the [Implications of Slow or Floating CMOS Inputs](#) application report.

Do not leave inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10-k Ω resistor is recommended and will typically meet all requirements.

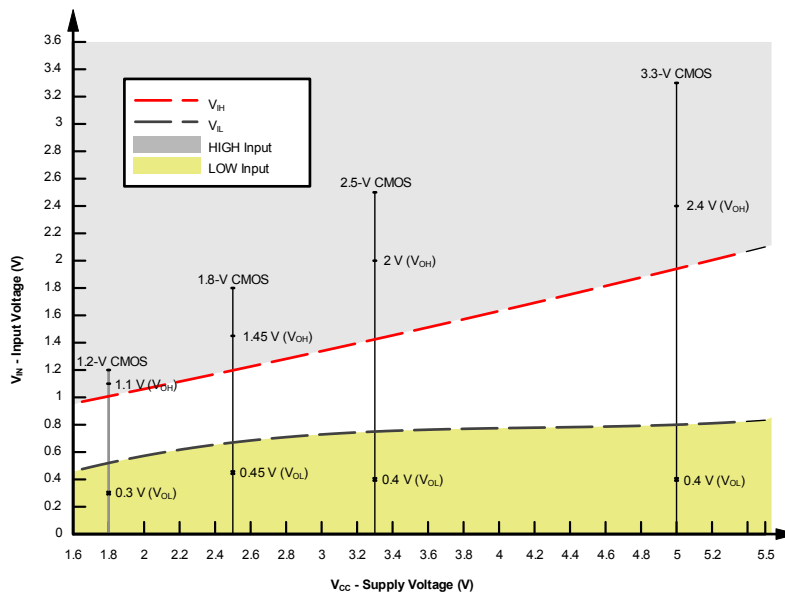


Figure 9-2. LVxT Input Voltage Levels

9.3.4.1 Down Translation

Signals can be translated down using the SN74LV6T17. The voltage applied at the V_{CC} will determine the output voltage and the input thresholds as described in the *Recommended Operating Conditions* and *Electrical Characteristics* tables.

When connected to a high-impedance input, the output voltage will be approximately V_{CC} in the HIGH state, and 0 V in the LOW state. As shown in [Figure 9-2](#), ensure that the input signals in the HIGH state are between $V_{IH(MIN)}$ and 5.5 V, and input signals in the LOW state are lower than $V_{IL(MAX)}$.

As shown in [Figure 9-3](#) for example, the standard CMOS inputs for devices operating at 5.0 V, 3.3 V or 2.5 V can be down-translated to match 1.8 V CMOS signals when operating from 1.8-V V_{CC} .

Down Translation Combinations are as follows:

- 1.8-V V_{CC} – Inputs from 2.5 V, 3.3 V, and 5.0 V
- 2.5-V V_{CC} – Inputs from 3.3 V and 5.0 V
- 3.3-V V_{CC} – Inputs from 5.0 V

9.3.4.2 Up Translation

Input signals can be up translated using the SN74LV6T17. The voltage applied at V_{CC} will determine the output voltage and the input thresholds as described in the *Recommended Operating Conditions* and *Electrical Characteristics* tables. When connected to a high-impedance input, the output voltage will be approximately V_{CC} in the HIGH state, and 0 V in the LOW state.

The inputs have reduced thresholds that allow for input HIGH state levels which are much lower than standard values. For example, standard CMOS inputs for a device operating at a 5-V supply will have a $V_{IH(MIN)}$ of 3.5 V. For the SN74LV6T17, $V_{IH(MIN)}$ with a 5-V supply is only 2 V, which would allow for up-translation from a typical 2.5-V to 5-V signals.

As shown in [Figure 9-3](#), ensure that the input signals in the HIGH state are above $V_{IH(MIN)}$ and input signals in the LOW state are lower than $V_{IL(MAX)}$.

Up Translation Combinations are as follows:

- 1.8-V V_{CC} – Inputs from 1.2 V
- 2.5-V V_{CC} – Inputs from 1.8 V
- 3.3-V V_{CC} – Inputs from 1.8 V and 2.5 V
- 5.0-V V_{CC} – Inputs from 2.5 V and 3.3 V

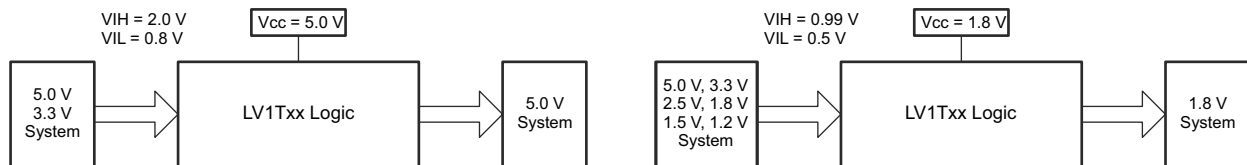


Figure 9-3. LVxT Up and Down Translation Example

9.3.5 Wettable Flanks

This device includes wettable flanks for at least one package. See the *Features* section on the front page of the data sheet for which packages include this feature.

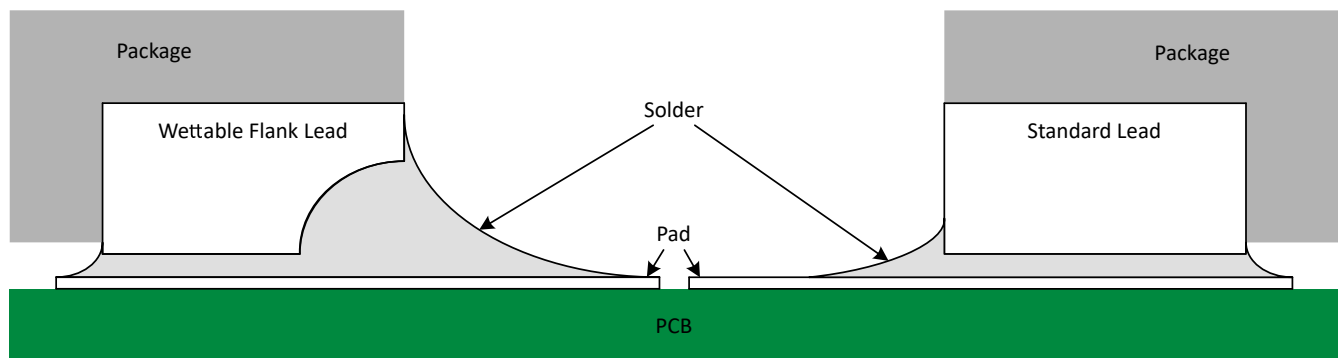


Figure 9-4. Simplified Cutaway View of Wettable-Flank QFN Package and Standard QFN Package After Soldering

Wettable flanks help improve side wetting after soldering, which makes QFN packages easier to inspect with automatic optical inspection (AOI). As shown in [Figure 9-4](#), a wettable flank can be dimpled or step-cut to provide

additional surface area for solder adhesion which assists in reliably creating a side fillet. See the mechanical drawing for additional details.

9.4 Device Functional Modes

表 9-1 lists the functional modes of the SN74LV6T17.

表 9-1. Function Table

| INPUT A ⁽¹⁾ | OUTPUT Y |
|------------------------|----------|
| H | H |
| L | L |

(1) H = high voltage level, L = low voltage level, X = do not care, Z = high impedance

10 Application and Implementation

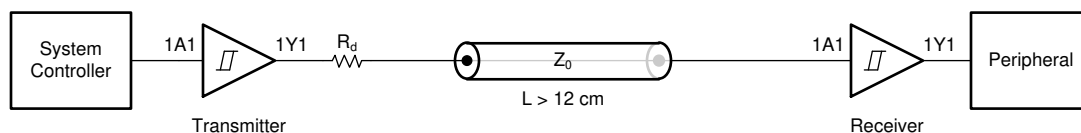
注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

10.1 Application Information

The SN74LV6T17 can be used to drive signals over relatively long traces or transmission lines. In order to reduce ringing caused by impedance mismatches between the driver, transmission line, and receiver, a series damping resistor placed in series with the transmitter's output can be used. The figure in the *Application Curve* section shows the received signal with three separate resistor values. Just a small amount of resistance can make a significant impact on signal integrity in this type of application.

10.2 Typical Application



✎ 10-1. Typical Application Block Diagram

10.2.1 Design Requirements

10.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LV6T17 plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LV6T17 plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74LV6T17 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74LV6T17 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in the [CMOS Power Consumption and Cpd Calculation](#) application note.

Thermal increase can be calculated using the information provided in the [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#) application note.

注意

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

10.2.1.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LV6T17 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k Ω resistor value is often used due to these factors.

The SN74LV6T17 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

10.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

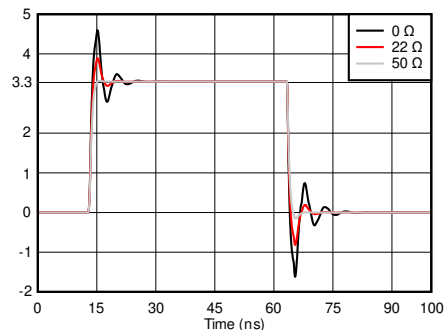
Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

10.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV6T17 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)}) \Omega$. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in $M\Omega$; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

10.2.3 Application Curves



✎ 10-2. Simulated Signal Integrity at the Receiver With Different Damping Resistor (R_d) Values

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices, inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused (for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used). Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

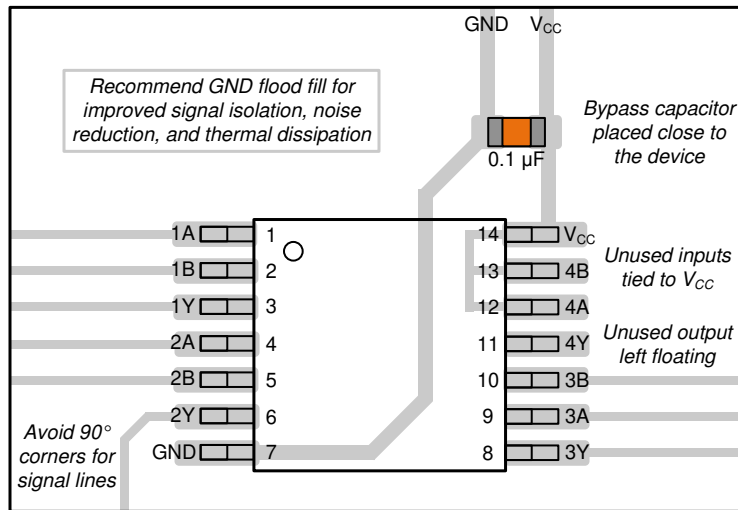


图 11-1. Example Layout for the SN74LV6T17

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and Cpd Calculation application note](#)
- Texas Instruments, [Designing With Logic application note](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application note](#)
- Texas Instruments, [Implications of Slow or Floating CMOS Inputs application note](#)

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12.3 サポート・リソース

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12.6 用語集

[テキサス・インスツルメンツ用語集](#) この用語集には、用語や略語の一覧および定義が記載されています。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

| Orderable Device | Status (1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan (2) | Lead finish/ Ball material (6) | MSL Peak Temp (3) | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|---------------|--------------|-----------------|------|-------------|-----------------|--------------------------------------|----------------------|--------------|-------------------------|-------------------------|
| SN74LV6T17BQAR | ACTIVE | WQFN | BQA | 14 | 3000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | LV6T17 | Samples |
| SN74LV6T17PWR | ACTIVE | TSSOP | PW | 14 | 3000 | RoHS & Green | NIPDAU SN | Level-1-260C-UNLIM | -40 to 85 | LV6T17 | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74LV6T17 :

- Automotive : [SN74LV6T17-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

GENERIC PACKAGE VIEW

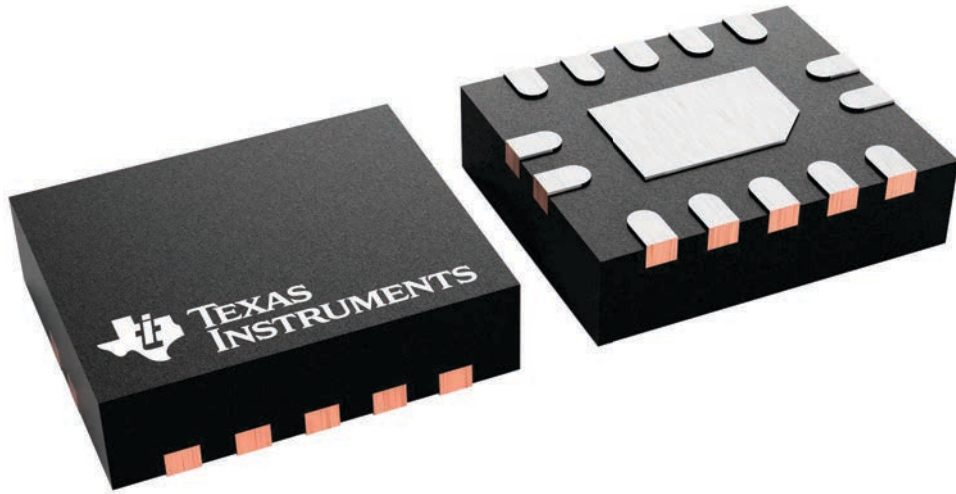
BQA 14

WQFN - 0.8 mm max height

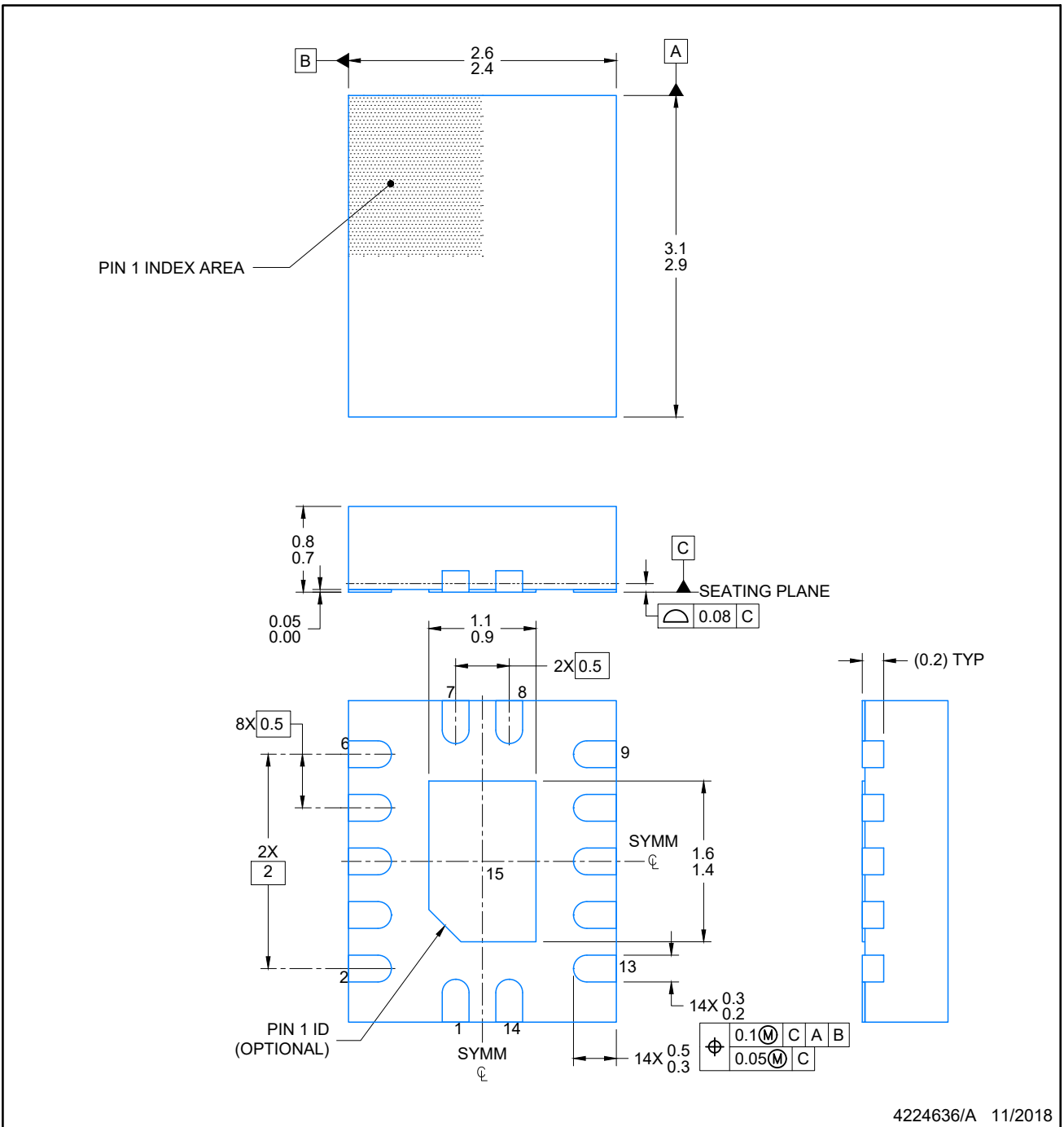
2.5 x 3, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4227145/A



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

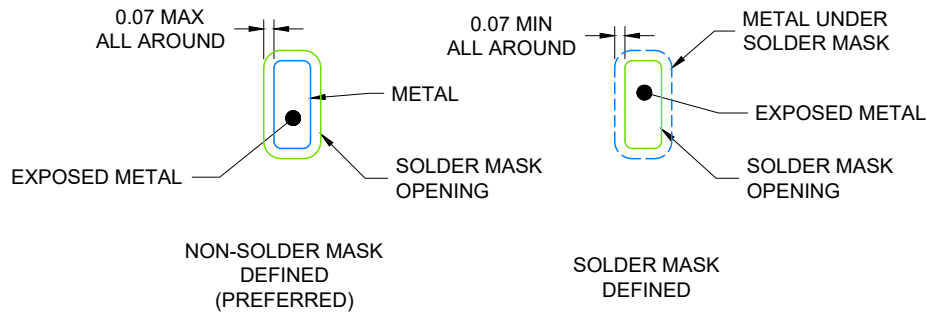
BQA0014A

WQFN - 0.8 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



4224636/A 11/2018

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

BQA0014A

WQFN - 0.8 mm max height

PLASTIC QUAD FLAT PACK-NO LEAD



SOLDER PASTE EXAMPLE
 BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
 88% PRINTED COVERAGE BY AREA
 SCALE: 20X

4224636/A 11/2018

NOTES: (continued)

- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PW0014A



PACKAGE OUTLINE
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



4220202/B 12/2023

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220202/B 12/2023

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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